

Patent

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Applicant(s): Tews et al.
Serial No.: 09/714,356
Filed: November 5, 2000
Entitled: Nitrogen Implantation Using A Shadow
Effect To Control Gate Oxide
Thickness In STI DRAM
Semiconductors

Group Art Unit: 2813

Examiner: Jack Chen

Docket No.: 00 P 9031 US

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On: February 21, 2002Signed: 

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Reg. No. 32,556

ELECTION

Assistant Commissioner for Patents
Washington, D.C. 20231

In response to the restriction requirement dated November 5, 2001, applicants elect to
prosecute claims 2, 4, 5 without traverse.

Respectfully submitted,



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FEB 21 2002

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